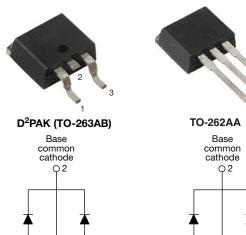
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SHA\

VS-20CTH03SHM3, VS-20CTH03-1HM3

Vishay Semiconductors

Hyperfast Rectifier, 2 x 10 A FRED Pt[®]



| 02 | 10 Common 03 Anode cathode Anode VS-20CTH03SHM3 1 Common 3 Anode cathode Anode VS-20CTH03-1HM3

2

LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS									
I _{F(AV)}	2 x 10 A								
V _R	300 V								
V _F at I _F	0.85 V								
t _{rr} typ.	23 ns								
T _J max.	175 °C								
Package	D ² PAK (TO-263AB), TO-262AA								
Circuit configuration	Common cathode								

FEATURES

- Hyperfast recovery time
- Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified, meets JESD 201, class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Vishay Semiconductors 300 V series are the state of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

MECHANICAL DATA

Case: D²PAK (TO-263AB), TO-262AA

Molding compound meets UL 94 V-0 flammability rating

Terminal: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS						
Peak repetitive reverse voltage		V _{RRM}		300	V					
Average rectified forward current —	per diode	I _{F(AV)}	T _C = 160 °C	10						
Average rectilied forward current —	per device			20	А					
Non-repetitive peak surge current		I _{FSM}	T _J = 25 °C	120						
Operating junction and storage temp	peratures	T _J , T _{Stg}		-55 to +175	°C					

ELECTRICAL SPECIFICATIONS ($T_J = 25$ °C unless otherwise specified)											
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS					
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	300	-	-	M					
Family and souther an	N	I _F = 10 A	-	1.05	1.25	UNITS - V - μΑ - pF - nH					
Forward voltage	V _F	I _F = 10 A, T _J = 125 °C	-	0.85	0.95						
Poveroa lookago ourrent		$V_{R} = V_{R}$ rated	-	-	20						
Reverse leakage current	I _R	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	6	200	μΑ					
Junction capacitance	CT	V _R = 300 V	-	30	-	pF					
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH					

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1

Document Number: 95671

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DYNAMIC RECOVERY CHARACTERISTICS ($T_C = 25$ °C unless otherwise specified)											
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS				
		I _F = 1.0 A, dI _F /dt =	100 A/µs, V _R = 30 V	-	23	-					
Reverse recovery time	t _{rr}	T _J = 25 °C		-	31	-	ns				
		T _J = 125 °C		-	42	-					
Peak recovery current	I	T _J = 25 °C	l _F = 10 A dl _F /dt = 200 A/µs	-	2.4	-	A				
Feat recovery current	I _{RRM}	T _J = 125 °C	$V_{\rm R} = 200 \text{ V}$	-	5.6	-					
Reverse recovery charge	Q _{rr}	T _J = 25 °C	VH - 200 V	-	36	-	nC				
neverse recovery charge	Q _{rr}	T _J = 125 °C		-	120	-	no				

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C				
Thermal resistance, junction to case per diode	R _{thJC}		-	-	1.5	°C/W				
Thermal resistance, junction to ambient	R _{thJA}		-	-	70	°C/W				
Weight			-	2.0	-	g				
weight			-	0.07	-	oz.				
Marking device		Case style D ² PAK (TO-263AB)	20CTH03SH							
		Case style TO-262AA	20CTH03-1H							

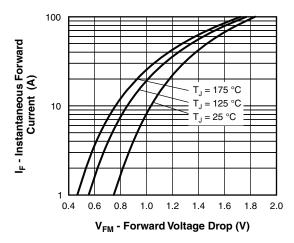


Fig. 1 - Maximum Forward Voltage Drop Characteristics

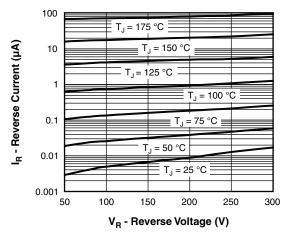


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



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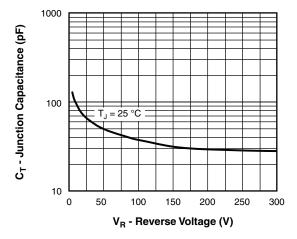


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

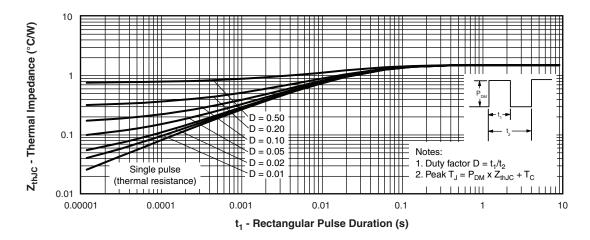
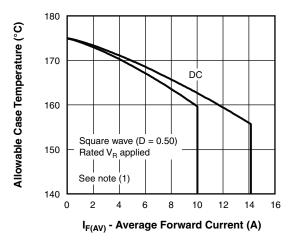


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

Average Power Loss (W)





Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \ \mathsf{x} \ \mathsf{V_{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \ \mathsf{x} \ \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

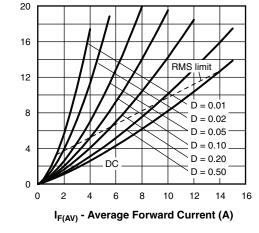


Fig. 6 - Forward Power Loss Characteristics

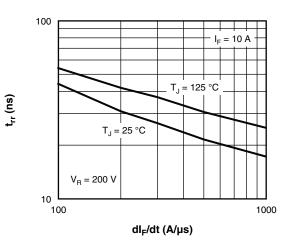
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Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

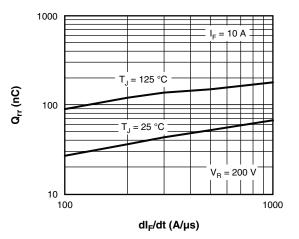


Fig. 8 - Typical Stored Charge vs. dl_F/dt

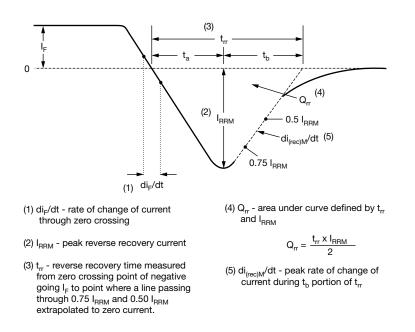


Fig. 9 - Reverse Recovery Waveform and Definitions



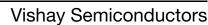
Vishay Semiconductors

ORDERING INFORMATION TABLE

Device code	vs-	20	С	т	н	03	S	TRL	н	М3		
		2	3	4	5	6	7	8	9	10		
	Vishay Semiconductors product											
	2.	- Current rating (20 A)										
	3 -		C = common cathode									
	4	- т=	TO-220	, D ² PAk	<							
	5 -	. Н=	hyperfa	ist rectifi	ier							
	6	- Volt	age rati	ng (03 =	= 300 V)							
	7.	• \$	= D ² PA	К								
		• -1	= TO-2	62								
	8 ·	• No	one = tu	be (50 p	oieces)							
		• TF	 TRL = tape and reel (left oriented, for D²PAK package) 									
		• TF	 TRR = tape and reel (right oriented, for D²PAK package) 									
	9.	• H=	AEC-Q	101 qua	lified							
	10 -	· МЗ	= halog	en-free,	RoHS-0	complia	nt, and	termina	tion lead	d (Pb)-fr		

LINKS TO RELATED DOCUMENTS									
Dimensions	D ² PAK (TO-263AB)	www.vishay.com/doc?95046							
Dimensions	TO-262AA	www.vishay.com/doc?95419							
	D ² PAK (TO-263AB)	www.vishay.com/doc?95444							
Part marking information	TO-262AA	www.vishay.com/doc?95443							
Packaging information	D ² PAK (TO-263AB)	www.vishay.com/doc?95032							
SPICE model		www.vishay.com/doc?96583							

Outline Dimensions

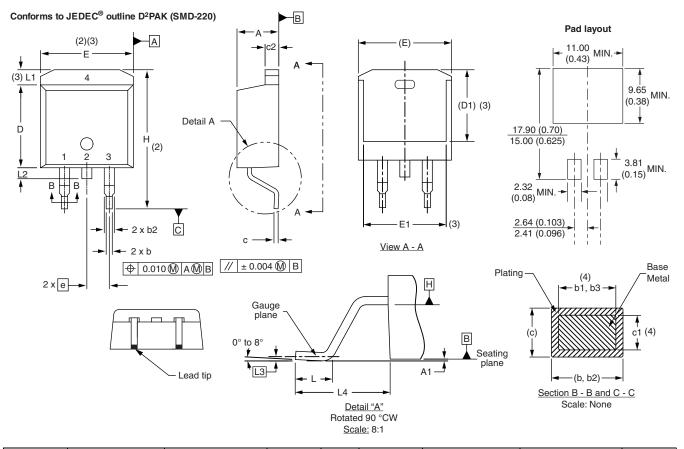


D²PAK

DIMENSIONS in millimeters and inches

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SYMBOL	MILLIM	IETERS	INC	HES	NOTES	SYMBOL	MILLIM	IETERS	INC	HES	NOTES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		STWDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

Revision: 08-Jul-15

1

Document Number: 95046

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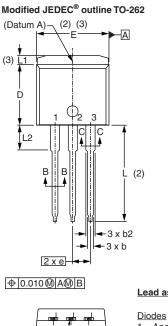
Outline Dimensions



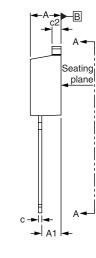
Vishay Semiconductors

TO-262

DIMENSIONS in millimeters and inches

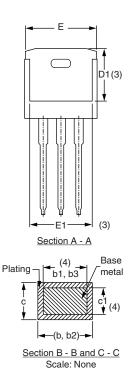


Lead tip -



Lead assignments

1. - Anode (two die)/open (one die) 2., 4. - Cathode 3. - Anode



MILLIMETERS INCHES SYMBOL NOTES MIN. MAX. MIN. MAX. А 4.06 4.83 0.160 0.190 2.03 A1 3.02 0.080 0.119 b 0.51 0.99 0.020 0.039 b1 0.51 0.89 0.020 0.035 4 b2 1.14 1.78 0.045 0.070 1.14 1.73 0.045 0.068 4 b3 0.38 0.74 0.015 0.029 С 0.38 0.58 0.015 0.023 4 c1 1.14 1.65 0.045 0.065 c2 D 8.51 9.65 0.335 0.380 2 D1 6.86 8.00 0.270 0.315 3 Е 9.65 10.67 0.380 0.420 2, 3 E1 7.90 8.80 0.311 0.346 3 0.100 BSC 2.54 BSC е L 13.46 14.10 0.530 0.555 L1 _ 1.65 0.065 3 _ 3.36 0.132 0.146 L2 3.71

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

(5) Controlling dimension: inches

(6) Outline conform to JEDEC TO-262 except A1 (maximum), b (minimum) , D1 (minimum) and L2 where dimensions derived the actual package outline

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